IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors

founded by NXP

BUJD203AX

NPN power transistor with integrated diode

Rev. 01 — 27 September 2010 | Product data sheet

1. Product profile

1.1 General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated anti-parallel E-C diode in a SOT186A (TO220F) full pack plastic package.

1.2 Features and benefits

- Fast switching
- High voltage capability
- Integrated anti-parallel E-C diode
- Isolated package
- Very low switching and conduction losses

1.3 Applications

- DC-to-DC converters
- Electronic lighting ballasts
- Inverters
- Motor control systems

1.4 Quick reference data

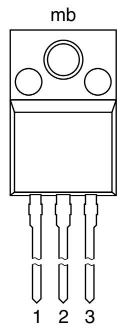
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_C	collector current	see Figure 1; see Figure 2; DC; see Figure 4	-	-	4	A
P_{tot}	total power dissipation	$T_h \leq 25$ °C; see Figure 3	-	-	26	W
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0$ V	-	-	850	V
Static characteristics						
h_{FE}	DC current gain	$I_C = 500$ mA; $V_{CE} = 5$ V; see Figure 11; $T_h = 25$ °C	13	21	32	
		$V_{CE} = 5$ V; $I_C = 3$ A; see Figure 11; $T_h = 25$ °C	-	12.5	-	
V_{CEOsus}	collector-emitter sustaining voltage	$I_B = 0$ A; $L_C = 25$ mH; $I_C = 10$ mA; see Figure 6; see Figure 7	400	450	-	V

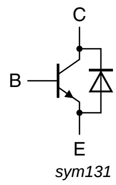
2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base		
2	C	collector		
3	E	emitter		
mb	n.c.	mounting base; isolated		



SOT186A (TO-220F)



3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUJD203AX	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CESM}	collector-emitter peak voltage	V_{BE} = 0 V	-	850	V
V_{CBO}	collector-base voltage	I_E = 0 A	-	850	V
V_{CEO}	collector-emitter voltage	I_B = 0 A	-	425	V
I_C	collector current	DC; see Figure 1; see Figure 2; see Figure 4	-	4	A
I_{CM}	peak collector current	see Figure 1; see Figure 2; see Figure 4	-	8	A
I_B	base current	DC	-	2	A
I_{BM}	peak base current		-	4	A
P_{tot}	total power dissipation	T_h ≤ 25 °C; see Figure 3	-	26	W
T_{stg}	storage temperature		-65	150	°C
T_j	junction temperature		-	150	°C

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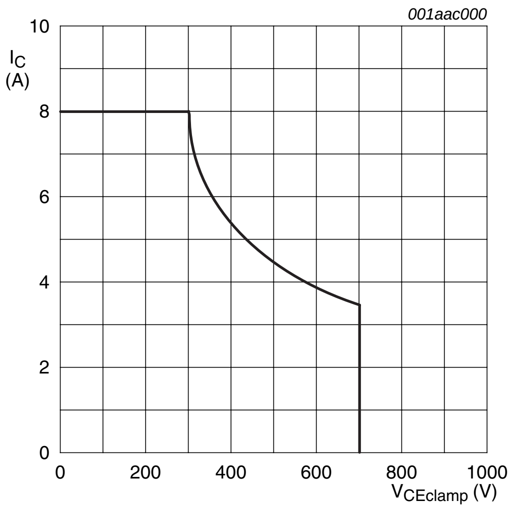
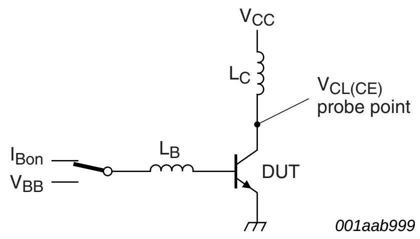


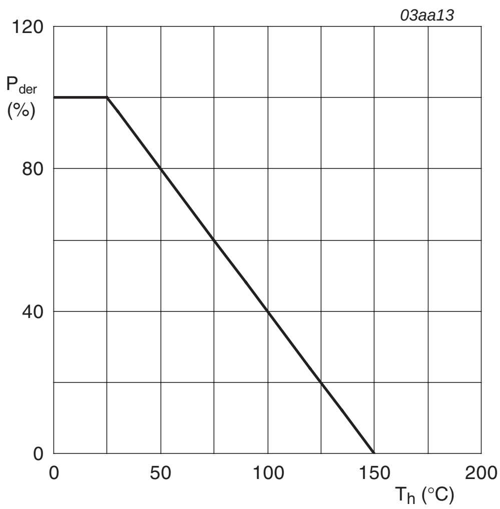
$T_j \leq T_{j(max)}$ °C

Fig 1. Reverse bias safe operating area



$V_{CL(CE)} \leq 1000\ V; V_{CC} = 150\ V; V_{BB} = -5\ V;$
$L_B = 1\ \mu H; L_C = 200\ \mu H$

Fig 2. Test circuit for reverse bias safe operating area



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\ \%$$

Fig 3. Normalized total power dissipation as a function of heatsink temperature

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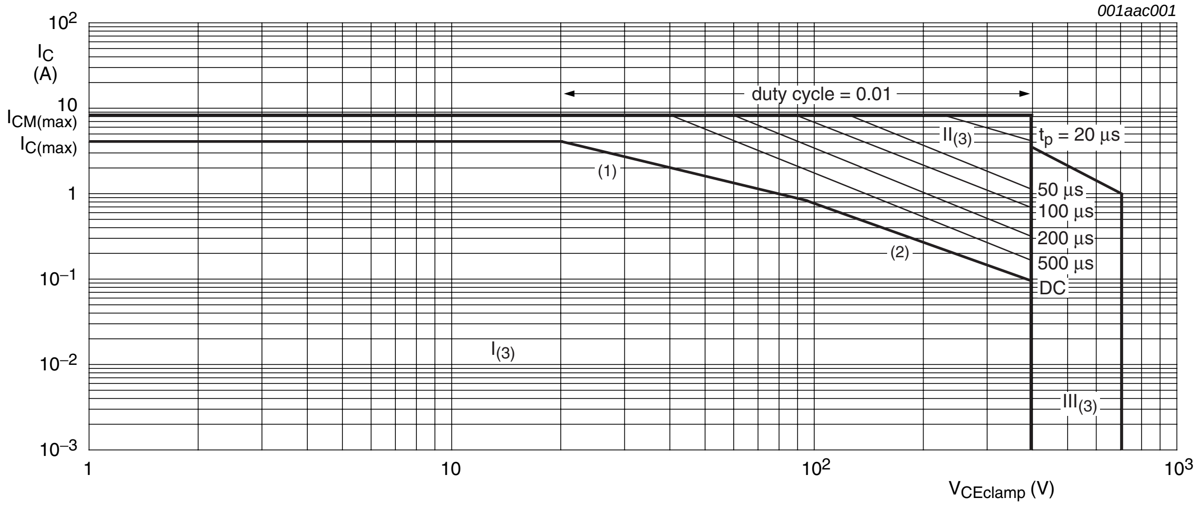

1)P_{tot} maximum and P_{tot} peak maximum lines

2)Second breakdown limits

3) I = Region of permissable DC operation

II = Extension for repetitive pulse operation

III = Extension during turn-on in single transistor converters provided that $R_{BE} \leq 100\ \Omega$ and $t_p \leq 0.6$ µs

Fig 4. Forward bias safe operating area for $T_{mb} \leq 25$ °C

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 5	-	-	4.8	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W

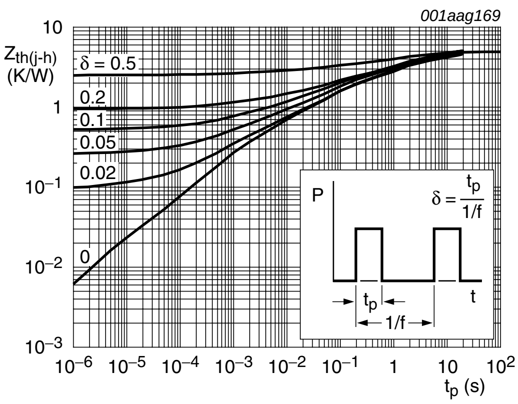

Fig 5. Transient thermal impedance from junction to heatsink as a function of pulse duration

6. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; T_h = 25 °C; from all terminals to external heatsink; clean and dust free	-	-	2500	V
C_{isol}	isolation capacitance	T_h = 25 °C; f = 1 MHz; from collector to external heatsink	-	10	-	pF

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7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{CES}	collector-emitter cut-off current	V_{BE} = 0 V; V_{CE} = 850 V; T_j = 125 °C	[1]	-	-	2	mA
		V_{BE} = 0 V; V_{CE} = 850 V; T_j = 25 °C	[1]	-	-	1	mA
I_{CBO}	collector-base cut-off current	V_{CB} = 850 V; I_E = 0 A	[1]	-	-	1	mA
I_{CEO}	collector-emitter cut-off current	V_{CE} = 425 V; I_B = 0 A	[1]	-	-	0.1	mA
I_{EBO}	emitter-base cut-off current	V_{EB} = 7 V; I_C = 0 A		-	-	10	mA
V_{CEOsus}	collector-emitter sustaining voltage	I_B = 0 A; I_C = 10 mA; L_C = 25 mH; see Figure 6; see Figure 7		400	450	-	V
V_{CEsat}	collector-emitter saturation voltage	I_C = 3 A; I_B = 0.6 A; see Figure 8; see Figure 9		-	0.29	1	V
V_{BEsat}	base-emitter saturation voltage	I_C = 3 A; I_B = 0.6 A; see Figure 10		-	0.99	1.5	V
V_F	forward voltage	I_F = 2 A; T_j = 25 °C		-	1.04	1.5	V
h_{FE}	DC current gain	I_C = 1 mA; V_{CE} = 5 V; T_h = 25 °C; see Figure 11		10	15	32	
		I_C = 500 mA; V_{CE} = 5 V; T_h = 25 °C; see Figure 11		13	21	32	
		I_C = 2 A; V_{CE} = 5 V; T_h = 25 °C; see Figure 11		11	16	22	
		I_C = 3 A; V_{CE} = 5 V; T_h = 25 °C; see Figure 11		-	12.5	-	
Dynamic characteristics							
t_{on}	turn-on time	I_C = 2.5 A; I_{Bon} = 0.5 A; I_{Boff} = -0.5 A; R_L = 75 Ω; T_j = 25 °C; resistive load; see Figure 12; see Figure 13		-	0.52	0.6	µs
t_s	storage time	I_C = 2.5 A; I_{Bon} = 0.5 A; I_{Boff} = -0.5 A; R_L = 75 Ω; T_j = 25 °C; resistive load; see Figure 12; see Figure 13		-	2.7	3.3	µs
		I_C = 2 A; I_{Bon} = 0.4 A; V_{BB} = -5 V; L_B = 1 µH; T_j = 25 °C; inductive load; see Figure 14; see Figure 15		-	1.2	1.4	µs
		I_C = 2 A; I_{Bon} = 0.4 A; V_{BB} = -5 V; L_B = 1 µH; T_j = 100 °C; inductive load; see Figure 14; see Figure 15		-	-	1.8	µs
t_f	fall time	I_C = 2.5 A; I_{Bon} = 0.5 A; I_{Boff} = -0.5 A; R_L = 75 Ω; T_j = 25 °C; resistive load; see Figure 12; see Figure 13		-	0.3	0.35	µs
		I_C = 2 A; I_{Bon} = 0.4 A; V_{BB} = -5 V; L_B = 1 µH; T_j = 100 °C; inductive load; see Figure 14; see Figure 15		-	-	0.12	µs
		I_C = 2 A; I_{Bon} = 0.4 A; V_{BB} = -5 V; L_B = 1 µH; T_j = 25 °C; inductive load; see Figure 14; see Figure 15		-	0.03	0.06	µs

[1] Measured with half-sine wave voltage (curve tracer)

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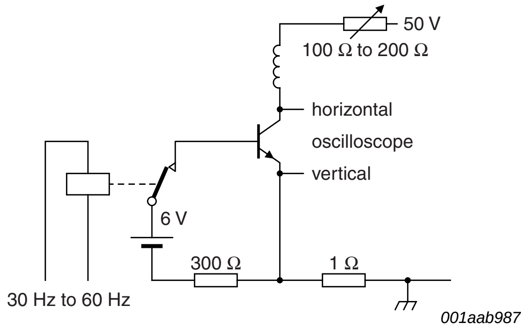


Fig 6. Test circuit for collector-emitter sustaining voltage

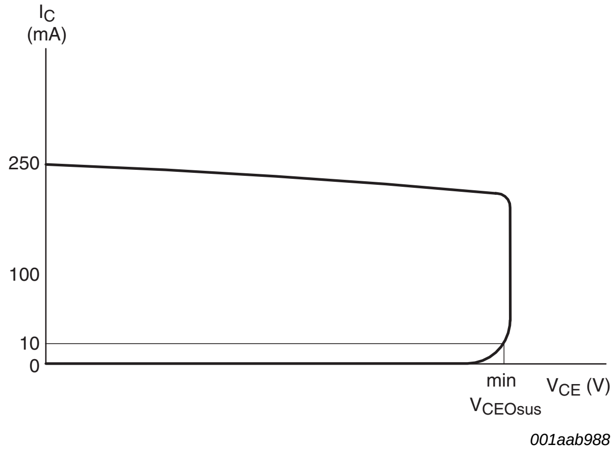
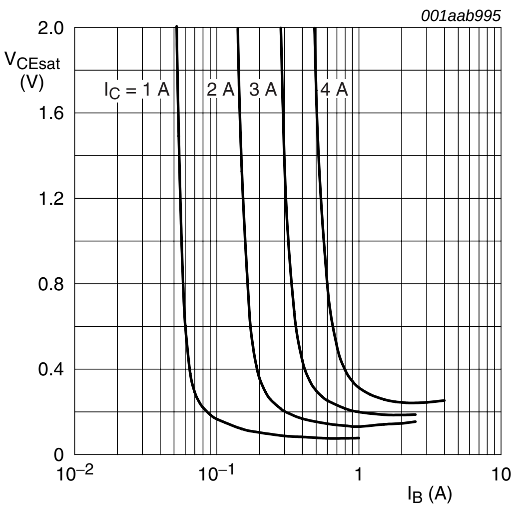
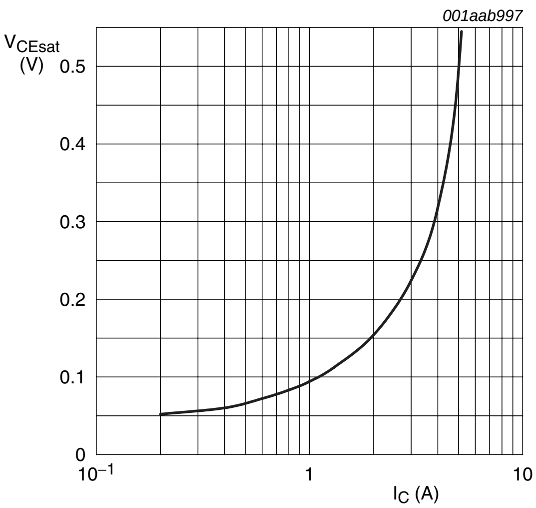


Fig 7. Oscilloscope display for collector-emitter sustaining voltage test waveform



$T_j = 25\ °C$

Fig 8. Collector-emitter saturation voltage as a function of base current; typical values



$I_C / I_B = 4$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values

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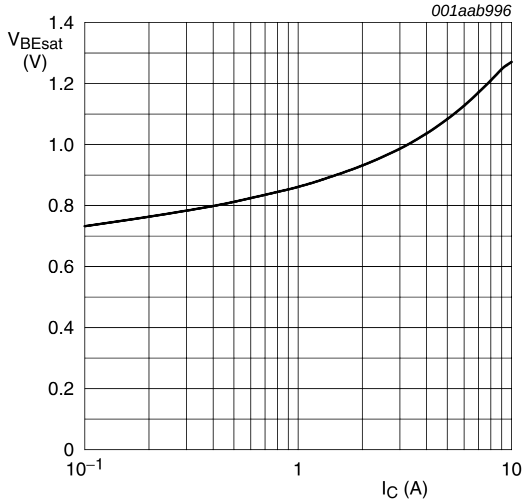
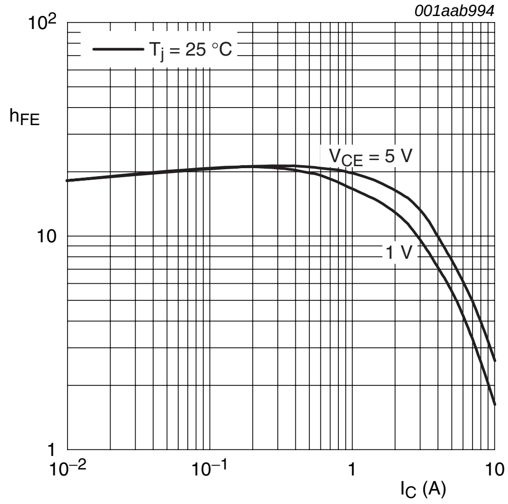


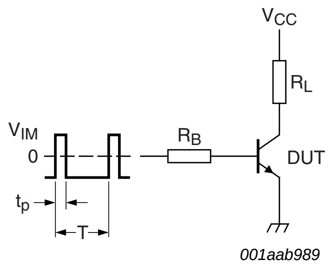
$I_C / I_B = 4$

Fig 10. Base-emitter saturation voltage as a function of collector current; typical values



$I_C / I_B = 4$

Fig 11. DC current gain as a function of collector current; typical values



$V_{IM} = -6$ to $+8$ V; $V_{CC} = 250$ V; $t_p = 20$ μs; $\delta = \frac{t_p}{T} = 0.01$

R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig 12. Test circuit for resistive load switching

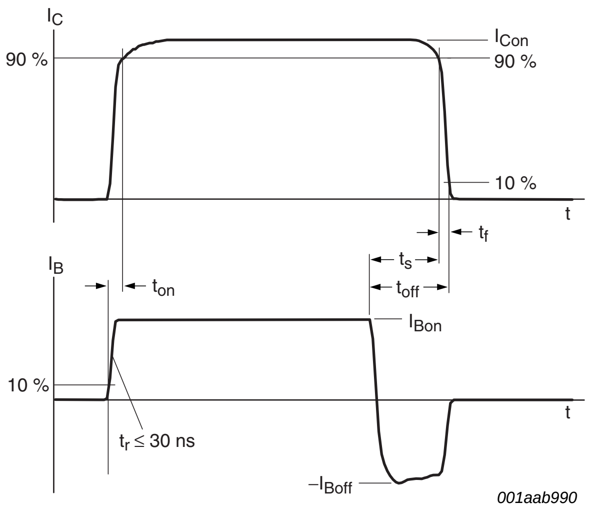


Fig 13. Switching times waveforms for resistive load

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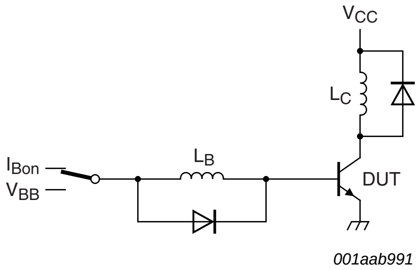

$V_{CC} = 300\ V; V_{BB} = -5\ V; L_C = 200\ \mu H; L_B = 1\ \mu H$

Fig 14. Test circuit for inductive load switching

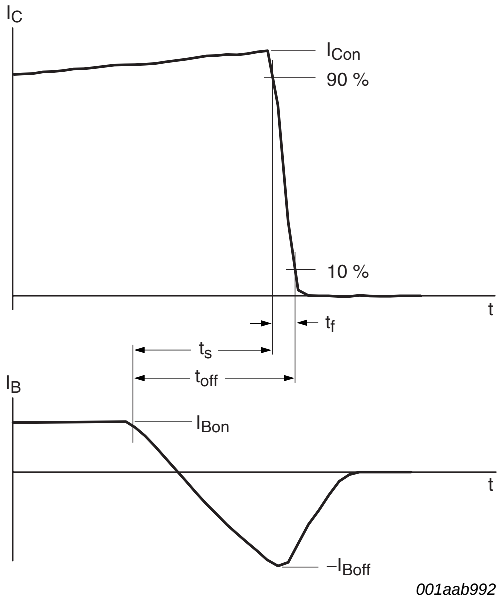

Fig 15. Switching times waveforms for inductive load

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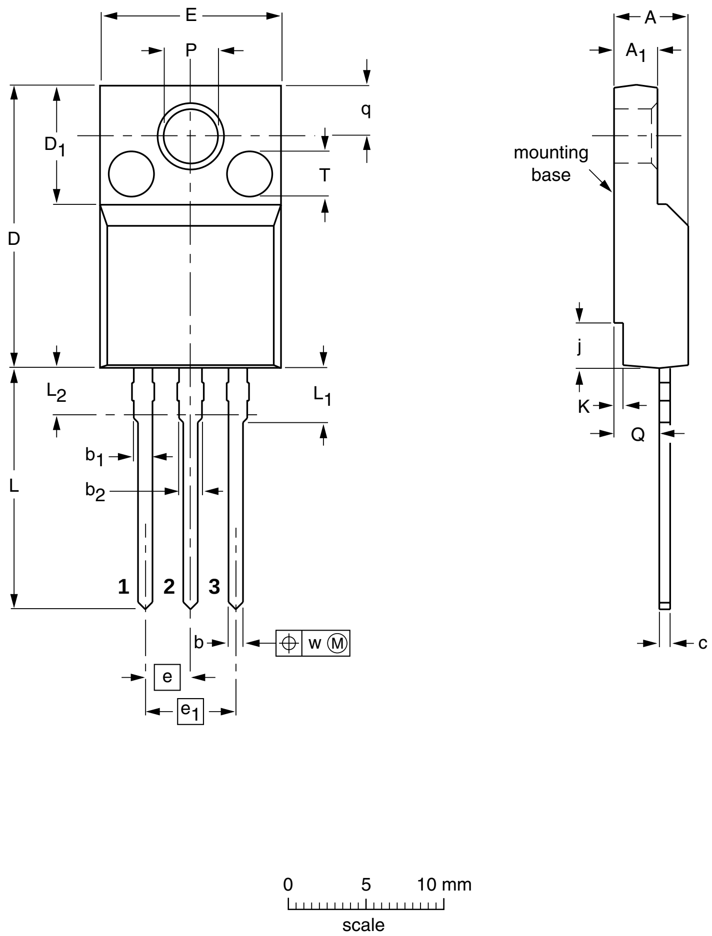
8. Package outline

Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1	b_2	c	D	D_1	E	e	e_1	j	K	L	L_1	$L_2^{(1)}$ max.	P	Q	q	$T^{(2)}$	w
mm	4.6 4.0	2.9 2.5	0.9 0.7	1.1 0.9	1.4 1.0	0.7 0.4	15.8 15.2	6.5 6.3	10.3 9.7	2.54	5.08	2.7 1.7	0.6 0.4	14.4 13.5	3.30 2.79	3	3.2 3.0	2.6 2.3	3.0 2.6	2.5	0.4

Notes

1. Terminal dimensions within this zone are uncontrolled.
2. Both recesses are ∅ 2.5 × 0.8 max. depth

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT186A		3-lead TO-220F				~~02-04-09~~ 06-02-14

Fig 16. Package outline SOT186A (TO-220F)

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9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUJD203AX v.1	20100927	Product data sheet	-	-

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10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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12. Contents

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